



**TAIYO NIPPON SAN SO**  
The Gas Professionals

# The Ultimate Gallium Nitride MOCVD System for High Quality Mass Production



**UR25K**

# Evolution of Productivity Improvement For Power, High Frequency, and LED Devices

## Advantages

- Based on the quality and uniformity-proven reactor of the atmospheric pressured SR series
- Automated parts handling system for the highest productivity
- Lowest cost of ownership by high growth rate epitaxy
- Highest throughput with the lowest downtime with Cl<sub>2</sub> dry cleaning equipment



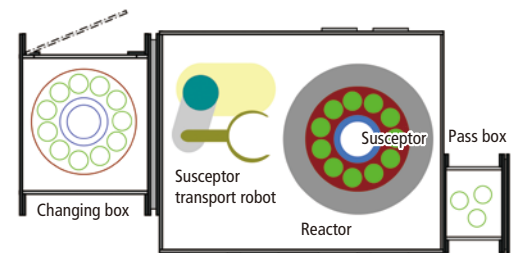
## UR25K Specifications

\*General specifications are listed below.

Reactor type	Face up, rotation & revolution
Wafer size	4" x 10 or 6" x 7
Heating system	Multi zone resistance heater
Sources	TMGa, TEGa, TMAI, TMIIn, NH <sub>3</sub> , Cp <sub>2</sub> Mg, SiH <sub>4</sub>
Gas nozzles	Three laminar flow horizontals
Transportation	Automatic susceptor unit transportation

\*Options: Cassette-to-Cassette System

## Transportation system

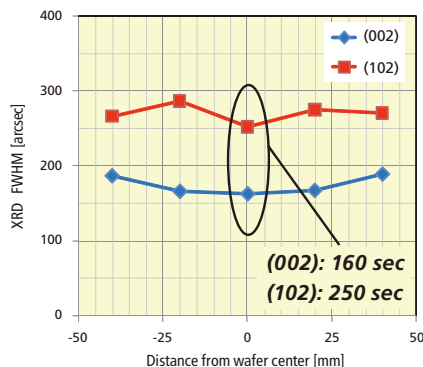


## Applications

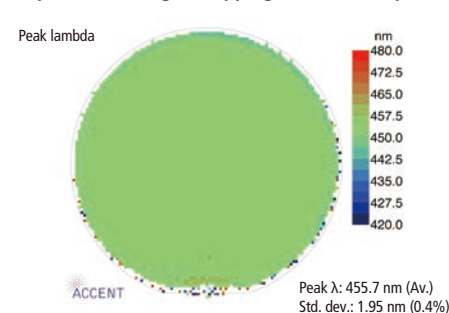
Epitaxial growth of GaN on Si (LED, Power device, etc.)

## Process data (at atmospheric pressure)

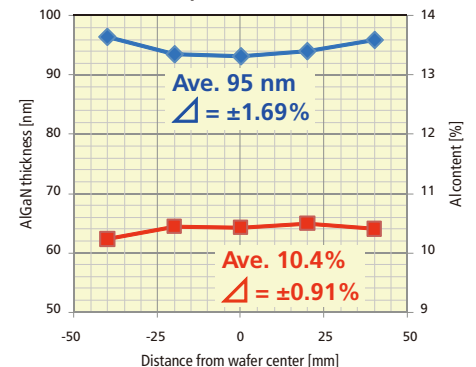
XRD FWHM of un-GaN



PL peak wavelength mapping of MQW sample



Thickness & Al comp. distribution of un-AlGaIn



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